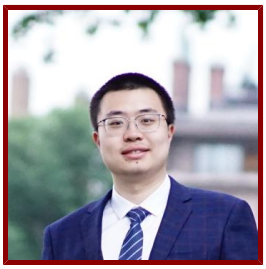
Stanford



Yanjie Shao

Assistant Professor of Electrical Engineering

Bio

ACADEMIC APPOINTMENTS

- Assistant Professor, Electrical Engineering

PROFESSIONAL EDUCATION

- Ph.D., Massachusetts Institute of Technology , Electrical Engineering (2023)
- B.S., University of Science and Technology of China , Physics (2019)

Publications

PUBLICATIONS

- **Discrete Ferroelectric Polarization Switching in Nanoscale Oxide-Channel Ferroelectric Field-Effect Transistors.** *Nano letters*
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- **Single-domain Switching Dynamics in BEOL Nanoscale Ferroelectric Field-effect Transistors**
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